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(54) **Title**: NON-PLANAR TRANSITOR FIN FABRICATION

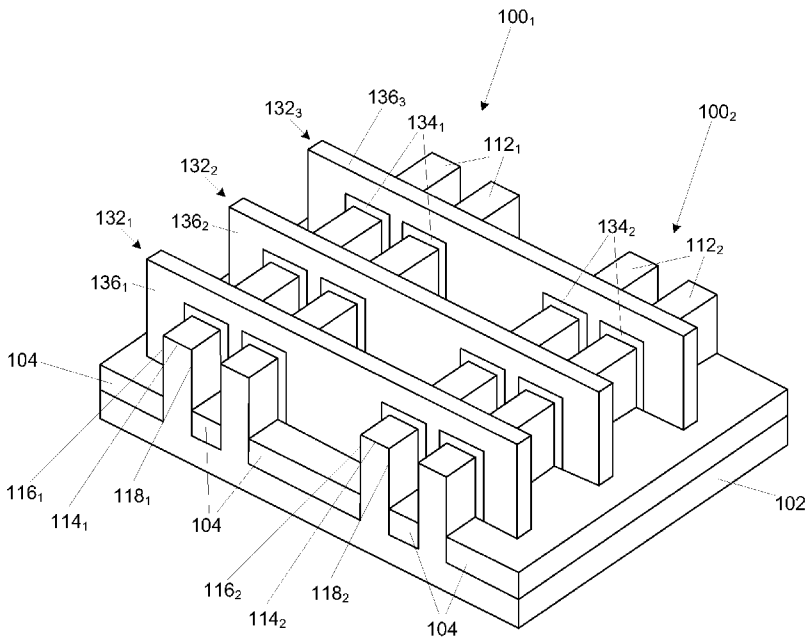


FIG. 1

(57) **Abstract**: The present description relates to the field of fabricating micro-electronic devices having non-planar transistors. Embodiments of the present description relate to the doping of fins within non-planar transistors, wherein a conformal blocking material layer, such as a dielectric material, may be used to achieve a substantially uniform doping throughout the non-planar transistor fins.

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